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## Table of Contents

<i>Preface</i>	<i>iii</i>
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### **Chapter 1 Design and Device Engineering**

Embedded Non-Volatile Memory Technologies <i>D. Shum (Infineon Technologies Taiwan Co. Ltd.)</i>	3
A Novel High Programming Efficiency and Highly Scalable Flash Memory Cell Based on Tunneling FET (TFET) <i>S. Qin, P. Tang, Y. Cai, Q. Huang, Y. Tang, and R. Huang (Peking University)</i>	9
Design of a 1-T Image Sensor by Simulation <i>X. Liu, S. Zang, X. Lin, C. Cao, P. Wang, and D. Zhang (Fudan University)</i>	17
Deposition of ZnO Films by Sputtering and its Resistive Switching Properties <i>F. Wang, K. Zhang, B. Yang, L. Wang, and K. Song (Tianjin University of Technology)</i>	25
Leakage Engineering Enabling PDSOI Ring Oscillators Operating in Sub-100pA/ $\mu$ m $I_{off}$ Regime <i>Z. Ren (IBM Semiconductor Research &amp; Development Center), J. Cai (IBM Research Division), R. R. Robison, B. Jagannathan (IBM Semiconductor Research &amp; Development Center), D. Park, and T. H. Ning (IBM Research Division)</i>	31

Ultra-Thin Body and BOX (UTBB) Device for Aggressive Scaling of CMOS Technology	37
<i>Q. Liu (STMicroelectronics), A. Yagishita (Toshiba), A. Kumar (IBM), N. Loubet (STMicroelectronics), T. Yamamoto (RENESAS Electronics), P. Kulkarni (IBM Research), F. Monsieur (STMicroelectronics), A. Khakifirooz, S. Ponoth, K. Cheng, B. Haran (IBM), M. Vinet (CEA-LETI), J. Cai (IBM Research Division), P. Khare, S. Monfray, F. Boeuf (STMicroelectronics), S. Mehta, J. Kuss (IBM), E. Leobandung (IBM Research), M. Hane (RENESAS Electronics), H. Bu (IBM Research), K. Ishimaru (Toshiba), T. Skotnicki, W. Kleemeier (STMicroelectronics), M. Takayanagi (Toshiba), T. Hook (IBM), M. Khare (IBM Research), S. Luning (GLOBALFOUNDRIES), B. Doris (IBM Research), and R. Sampson (STMicroelectronics)</i>	
Simulations of FDSOI CMOS with Sharing Contact between Source/Drain and Back Gate	43
<i>M. Xu, Q. Liang, H. Zhu, H. Yin, Z. Luo, D. Chen, and T. Ye (Chinese Academy of Sciences)</i>	
Scaling MOSFETs with Self-aligned Super-Steep-Retrograded Halo (3SRH)	49
<i>B. Wu, W. Xiao, H. Zhu, Q. Liang, H. Wu, H. Yin, Z. Luo (Chinese Academy of Sciences), H. Yu (Nanyang Technological University), D. Chen, and T. Ye (Chinese Academy of Sciences)</i>	
Electrostatic Discharge (ESD) Protection Challenges of Gate-All-Around Nanowire Field-Effect Transistors	55
<i>W. Liu, J. Liou (University of Central Florida), N. Singh, G. Lo (Agency for Science, Technology and Research), J. Chung, and Y. Jeong (Pohang University of Science and Technology)</i>	
Characterization of Random Telegraph Signal Effects for 0.18um Technology	61
<i>Y. Ji, S. Dai, M. Wei, X. Lu, S. Zhang, and D. Xu (Grace Semiconductor Manufacturing Corporation)</i>	
Effect of AlGaN Barrier Thickness on the Noise of AlGaN/GaN High Electron Mobility Transistors	67
<i>R. Yahyazadeh and Z. Hashempour (Islamic Azad University of Khoy Branch)</i>	
Extraction and Analysis of Substrate Parameters in On-Chip Spiral Inductor Model	75
<i>X. Li (East China Normal University), Z. Ren (Shanghai Integrated Circuits Research &amp; Development Center), D. Chen, and Y. Shi (East China Normal University)</i>	

Opportunities and Challenges of FinFET as a Device Structure Candidate for 14nm Node CMOS Technology	81
<i>T. Yamashita, V. Basker, T. Standaert, C. Yeh, J. Faltermeier (IBM Research), T. Yamamoto (RENESAS Electronics), C. Lin, A. Bryant (IBM Research), K. Maitra (GLOBALFOUNDRIES), P. Kulkarni, S. Kanakasabapathy (IBM Research), H. Sunamura (RENESAS Electronics), J. Wang, H. Jagannathan (IBM Research), A. Inada (RENESAS Electronics), J. Cho, R. Miller (GLOBALFOUNDRIES), B. Doris, V. Paruchuri, H. Bu, M. Khare, J. O'Neill, and E. Leobandung (IBM Research)</i>	
Structural effects of Channel Cross-Section on the Gate Capacitance of Silicon Nanowire Field-effect Transistors	87
<i>S. Sato, K. Kakushima, P. Ahmet (Tokyo Institute of Technology), K. Ohmori (University of Tsukuba), K. Natori (Tokyo Institute of Technology), K. Yamada (University of Tsukuba), and H. Iwai (Tokyo Institute of Technology)</i>	
Process Impact and Design Optimization on the Soft Yield of 25nm FinFET SRAM Cells	93
<i>M. Li, Q. Liang, H. Zhu, H. Zhong, D. Chen, and T. Ye (Chinese Academy of Sciences)</i>	
TiN/W/La <sub>2</sub> O <sub>3</sub> /Si High-k Gate Stack for EOT below 0.5nm	99
<i>P. Ahmet, D. Kitayama, T. Kaneda, T. Suzuki, T. Koyanagi, M. Kouda, M. Mamatrishat, T. Kawanago, K. Kakushima, K. Tsutsui, A. Nishiyama, N. Sugii, K. Natori, T. Hattori, and H. Iwai (Tokyo Institute of Technology)</i>	
PMOS Source/Drain Extension Dopant Species effect on Device and SRAM Performance	103
<i>J. Liu, J. Zhou, W. Wang, R. Guo, L. Zhang, Z. Shen, B. Wang, A. Zhou, H. Hao, J. Cui, and J. Ning (Semiconductor Manufacturing International Corporation)</i>	
A Novel Tunnel Oxide Based Tunnel FET	107
<i>H. Wang, Z. Luo, H. Yin, H. Zhu, J. Liu, and Z. Zhu (Chinese Academy of Sciences)</i>	
STI CMP: Exploration of a Colloidal Silica Based Slurry System	113
<i>P. Song, D. Yaoying, and J. Daw Sun (Anji Microelectronics (Shanghai) Co., Ltd.)</i>	
Linearity Improvement on MIM Capacitors	119
<i>T. Chu, P. Yang, E. S. Kho, Y. Ang, and S. Tia (X-FAB Sarawak Sdn. Bdn.)</i>	

Modeling of Electron Transport in III- Nitride Compound Semiconductors for Low Field and Low Temperature Applications <i>S. Chakrabarti, S. Gupta Chatterjee, D. Chattopadhyay, and S. Chatterjee (Techno India)</i>	125
Fast Flexible Electronics Based on Printable Thin Mono-Crystalline Silicon <i>Z. Ma, K. Zhang, J. Seo, H. Zhou, L. Sun, H. Yuan, G. Qin, H. Pang (University of Wisconsin Madison), and W. Zhou (University of Texas Arlington)</i>	137
HHNEC 0.18um BCD Technology for High Density Power Integration <i>Z. Shuai, Q. Wensheng, and D. Ke (Shanghai Hua Hong NEC Electronics Company, Limited)</i>	143
Performance Improvement of Si-NC Memory Device by Using a Novel Junction Assisted Programming Scheme <i>D. Jiang, Z. Huo, M. Zhang, Q. Wang, J. Liu, Z. Yu, X. Yang, Y. Wang (Chinese Academy of Sciences), B. Zhang (Grace Semiconductor Manufacturing Corporation), J. Chen (Anhui University), and M. Liu (Chinese Academy of Sciences)</i>	149
Dual Floating Gate Flash Cell Using Single Poly Processes <i>X. Lin (Fudan University), L. Liu (Oriental Semiconductor Co. Ltd.), X. Liu, S. Zanga, C. Cao, P. Wang, and D. Zhang (Fudan University)</i>	155
Anomalous Behaviors of Cubic GaInN Ternary Alloys <i>N. Tit (United Arab Emirates University)</i>	161
0.18um Scalable 7~45V pLDMOS for Smart Power Application <i>Z. Liu, S. Tang, J. Shen, and C. Shao (Grace Semiconductor Manufacturing Corporation)</i>	167
0.18 Micron BiCMOS Process with Novel Structure SiGeC HBT <i>D. Liu, W. Qian, X. Chen, F. Chen, J. Hu, S. Xiao, Y. Wang, and T. Chiu (HHNEC)</i>	173
Temperature Insensitive Clock Buffer and Its Application on Clock Tree <i>M. Tie and X. Li (IBM Systems &amp; Technology Group)</i>	183
Low-Power Design of Double Edge-Triggered Static SOI D Flip-Flop <i>W. Xing, J. Song, and D. Gang (Peking University)</i>	189
Effects of Oxygen Flow Ratios and Annealing on TiO <sub>x</sub> Deposited by Reactive Magnetron Sputtering <i>L. Wang, K. Zhang, Q. Wang, F. Wang, and X. Wei (Tianjin University of Technology)</i>	195

## Chapter 2

### Lithography and Patterning

Robustness Enhancement in Optical Lithography: From Pixelated Mask Optimization to Pixelated Source-Mask Optimization <i>N. Jia and E. Y. Lam (The University of Hong Kong)</i>	203
Mask Synthesis for Aerial Image Fidelity in Optical Lithography Using a Coarse-Grid-Approximation Level-Set Approach <i>Y. Peng, J. Zhang, Y. Wang, and Z. Yu (Tsinghua University)</i>	209
A Fast OPC Algorithm for IC Layout Based on 1-D Cells after Optimization of Gap Distribution <i>B. Lin, C. Xie, and Z. Shi (Zhejiang University)</i>	215
Extension Use of Immersion Lithography for the 22nm Half-Pitch and Beyond <i>R. Kanaya (Nikon Corporation)</i>	223
Cymer LPP EUV Source System Development Status <i>B. Lin (Cymer Southeast Asia Ltd.), B. La Fontaine, D. Brandt, and N. Farrar (Cymer Inc.)</i>	231
Advanced Packaging Stepper for 300mm Wafer Process <i>Z. Chang and H. Ling (Shanghai Micro Electronics Equipment Co., Ltd.)</i>	237
Foundry Efficiency Gains Through Common Photolithography Themes <i>J. E. Lamb III, C. Chris, Z. Zhu, D. Drain, and D. Sullivan (Brewer Science, Inc.)</i>	243
Use of DBARCs Beyond Implant <i>C. Washburn, J. A. Lowes, and A. Guerrero (Brewer Science, Inc.)</i>	249
Development of Under Layer Material for EUV Lithography <i>R. Sakamoto, B. Ho, N. Fujitani, T. Endo, and R. Ohnishi (Nissan Chemical Industries, Ltd.)</i>	257
Evaluation of 193 nm Photoresist Material at Advanced Immersion Nodes <i>J. Hao, Y. Xu, and C. Liu (Semiconductor Manufacturing International Corporation)</i>	263
Limit of Line End Shortening Correction under Single Exposure in 193 nm Immersion Lithography <i>Q. Wu, Y. Xu, J. Hao, C. Liu, X. Shi, and Y. Gu (Semiconductor Manufacturing International Corporation)</i>	269

248nm Process Is Capable for sub 0.09 um Groundrules <i>L. Wang, X. Guo, Y. Tong, H. Meng, B. Su, and S. Xiao (Shanghai HuaHong NEC Electronic Company Ltd.)</i>	277
Study to Transfer 0.11 $\mu$ m DRAM ArF Process to KrF Process in Litho <i>J. Liu, E. Yao, E. Fan, K. Chang, T. Lv, J. Zhang, L. Liang, J. Hong, and M. Li (Semiconductor Manufacturing International Corporation)</i>	285
Studying Photoresist Type for Sub-32nm Node Dense SRAM 2nd GT Layer <i>Y. Xu, J. Hao, C. Liu, X. Shi, Q. Wu, and Y. Gu (Semiconductor Manufacturing International Corporation)</i>	303

### **Chapter 3** **Dry and Wet Etch and Cleaning**

Selective Removal of High-k Dielectrics <i>D. Shamiryan and V. Paraschiv (imec)</i>	311
Active Area Width and Topography Effects on Sub 45nm Poly Gate CD <i>M. Shen, X. Meng, Y. Huang, H. Zhang, S. Chang, K. Lee, and Y. Gu (Semiconductor Manufacturing International Corporation)</i>	319
Reverse Phase Solution for Mesa Chamber Uniformity Improvement <i>Q. Ge, Y. Huang, and X. Tang (Semiconductor Technology Group Applied Materials China Globe Account)</i>	325
Plasma Etch Challenges for Porous Low k Materials for 32nm and Beyond <i>C. Labelle (GLOBALFOUNDRIES), R. Srivastava (GLOBALFOUNDRIES Singapore), J. C. Arnold, Y. Yin (IBM Research), M. Ishikawa (Toshiba America Electronic Components, Inc.), Y. Mignot (STMicroelectronics), H. Yusuff (IBM Microelectronics), J. Linville (GLOBALFOUNDRIES), D. Horak, N. Fuller (IBM Research), R. Patz, A. Darlak, K. Zhou, Y. Zhou, and J. Pender (Applied Materials)</i>	329
Dry Etch Process Effects on Cu/low-k Dielectric Reliability for Advanced CMOS Technologies <i>J. Zhou, W. Sun, H. Zhang, M. Hu, F. Li, X. Song, S. Chang, and K. Lee (Semiconductor Manufacturing International Corporation)</i>	335
New Al Post-Etch Residue Remover with Al Surface Passivation Function <i>J. C. Wei and M. Huang (DuPont Electronics and Communications)</i>	343

WAT and VBD Distribution Improvement on Low-K Trench All-in-one Process	349
<i>J. Hendrianto, H. Zhijie (Lam Research Corporation), and A. Liu (Semiconductor Manufacturing International Corporation)</i>	
Clean Mode Al Etch Process Development for Defect Reduction	355
<i>F. Qiang, C. Huang, J. Hendrianto (Lam Research Corporation), J. Song, M. Lv, K. Wang, and C. Shi (Semiconductor Manufacturing International Corporation)</i>	
Dummy Poly Silicon Gate Removal by Wet Chemical Etching	361
<i>T. Young, H. Yin, Q. Xu, C. Zhao, J. Li, and D. Chen (Chinese Academy of Sciences)</i>	
Theoretical And Experimental Development Of Advanced Dopant-Sensitive Systems	365
<i>P. Zhang (Qingdao Feiyang Vocational &amp; Technical College), L. Zhang (China Electronics Technology Group Corporation), Y. Ye (Nanjing University), and Y. Yang (China Electronics Technology Group Corporation)</i>	
Ultrapure Water-Related Problems and Waterless Cleaning Challenges	371
<i>T. Hattori (n/a)</i>	
Dry Etch Fin Patterning of a Sub-22nm Node SRAM Cell: EUV Lithography New Dry Etch Challenges	377
<i>E. Altamirano-Sanchez (imec), Y. Yamaguchi, J. Lindain (Lam Reseach), N. Horiguchi, M. Ercken, M. Demand, and W. Boullart (imec)</i>	
Effect of O <sub>2</sub> /Ar Ratio on Etching of Diamond Films by MPCVD	383
<i>S. Wang, K. Zhang, Z. Taofeng, and J. Ren (Tianjin University of Technology)</i>	
Porous SiOCH Integration: Etch Challenges with a Trench First Metal Hard Mask Approach	389
<i>N. Possémé, T. David (CEA-LETI), T. Chevolleau, M. Darnon (CNRS-LTM), P. Brun, M. Guillermet (CEA-LETI), J. Oddou (ST Microelectronics), S. Barnola (CEA-LETI), F. Bailly, R. Bouyssou (ST Microelectronics), J. Ducote (CNRS-LTM), R. Hurand (CEA-LETI), C. Vérove (ST Microelectronics), and O. Joubert (CNRS-LTM)</i>	
Plasma Etching Parameters Impact To Low-k Damage	395
<i>J. Zhang, H. Pei, and L. Cheng (Lam Research Corporation)</i>	

Prevention of AlCu Line Galvanic Corrosion after Fluoride Containing Stripper Cleaning: A Case Study	399
<i>V. Luo, J. Chang, K. Shi (Semiconductor Manufacturing International Corporation), B. Liu, L. Peng, A. Wang, and J. Sun (Anji Microelectronics (Shanghai) Co., Ltd.)</i>	
Highly Selective Etching Solutions for Advanced Logic Technologies	405
<i>X. Wang, H. Zhang, S. Chang, and K. Lee (Semiconductor Manufacturing International Corporation)</i>	
Discovering Practical Use of Sensor Wafers in CCP Reactors	409
<i>A. Milenin, M. Demand, W. Boullart (imec), and P. Arleo (KLA-Tencor)</i>	
Study on Silicon Sieve Holes Array for Future Lithography Application	415
<i>W. Si, M. Yin (Tsinghua University), J. Qin (Hunan University), and Z. Liu (Tsinghua University)</i>	
Controlled Etching of III-V Materials with Optical Emission Interferometry (OEI)	421
<i>C. Johnson, D. Johnson, R. Westerman, D. Geerpuram, L. Martinez, and J. Plumhoff (Plasma-Therm LLC)</i>	
Low Silicon and SiGe Loss in High Dose Implant Resist Strip	427
<i>X. Meng, M. Shen, Y. Huang, H. Zhang, S. Chang, and K. Lee (Semiconductor Manufacturing International Corporation)</i>	
Effluent Management for Non-Oxidizing Plasma Strip Processes	433
<i>S. Luo, C. Waldfried, O. Escoria, I. Berry, P. Geissbühler, A. Srivastava, and D. Roh (Axcelis Technologies, Inc.)</i>	
Wafer Backside Particle Reduction By Optimizing AC3 Coating for Poly Etch Chamber	439
<i>B. Ma, W. Liu (Lam Research Co., Ltd), F. Niu, J. Xia (Semiconductor Manufacturing International Corporation), L. Cheng (Lam Research Co., Ltd), and K. Liang (Semiconductor Manufacturing International Corporation)</i>	
The Study of Dry Etching Process on Plasma Induced Damage in Cu Interconnects Technology	445
<i>J. Zhou, H. Zhang, W. Sun, X. Wang, M. Hu, F. Li, L. Fu, S. Chang, and K. Lee (Semiconductor Manufacturing International Corporation)</i>	

## **Chapter 4**

### **Thin Film Technology**

Selective Epitaxial Growth: Trends in a Modern Transistor Device Fabrication <i>A. Y. Hikavyy, W. Vanherle, J. Dekoster, L. Witters, T. Hoffmann, and R. Loo (imec)</i>	455
Electron States at Interfaces of Semiconductors and Metals with Insulating Films <i>V. V. Afanas'ev, M. Houssa, and A. Stesmans (University of Leuven)</i>	467
Atomic-Layer Deposition of Lutetium Aluminate Thin Films for Non-Volatile Memory Applications <i>C. Adelmann, J. Swerts, T. Conard, B. Brijs, A. Franquet (imec), A. Hardy (Hasselt University), H. Tielens, K. Opsomer, A. Moussa (imec), M. K. Van Bael (Hasselt University), M. Jurczak, J. A. Kittl, and S. Van Elshocht (imec)</i>	473
Evolution of STI Gap Fill Technology <i>J. C. Chen, Y. Chen, R. Gao, C. Cheng, X. Li, G. Zhao (Applied Materials China), D. Chan, and T. Lee (Applied Materials)</i>	479
Annealing Effect on the Electrical Properties of La <sub>2</sub> O <sub>3</sub> /InGaAs MOS Capacitors <i>T. Kanda, D. Zade (Tokyo Institute of Technology), Y. C. Lin (National Chiao-Tung University), K. Kakushima, P. Ahmet, K. Tsutsui, A. Nishiyama, N. Sugii (Tokyo Institute of Technology), E. Y. Chang (National Chiao-Tung University), K. Natori, T. Hattori, and H. Iwai (Tokyo Institute of Technology)</i>	483
Metal Inserted Poly-Si Stacks with La <sub>2</sub> O <sub>3</sub> Gate Dielectrics for Scaled EOT and V <sub>FB</sub> Control by Oxygen Incorporation <i>T. Kawanago, K. Kakushima, P. Ahmet, K. Tsutsui, A. Nishiyama, N. Sugii, K. Natori, T. Hattori, and H. Iwai (Tokyo Institute of Technology)</i>	489
Characteristics of HfSiAlON Gate Dielectric Prepared by Physical Vapor Deposition <i>G. Xu and Q. Xu (Chinese Academy of Sciences)</i>	495
Deposition of VO <sub>X</sub> Films by Reactive Sputtering and its Properties <i>X. Wei, K. Zhang, W. Fang, L. Wang, Y. Zhang, and K. Song (Tianjin University of Technology)</i>	503

ALD Ru and its Application in DRAM MIM-Capacitors and Interconnect <i>M. Schaekers, J. Swerts, L. Altimime, and Z. Tökei (imec)</i>	509
Evaluation of Metallization Options for Advanced Cu Interconnects Application <i>N. Jourdan, L. Carbonell, N. Heylen, J. Swerts, S. Armini, A. Caro, S. Demuynck, K. Croes, G. Beyer, Z. Tökei, S. Elshocht, and E. Vancoille (imec)</i>	515
Fine Pitch Micro-Bump Interconnections for Advanced 3D Chip Stacking <i>W. Zhang, P. Limaye, A. La Manna, E. Beyne, and P. Soussan (imec)</i>	523
Temperature and Stress effects on IMC Behavior of Thin Film Cu-Al System in Wire Bond <i>X. Ming (CETC 58th Research Institute) and K. Fan (ASM Pacific Technology)</i>	529
Review of Silicon Nanowire Oxidation <i>X. Shi, R. Kurstjens, I. Vos, J. Everaert, and M. Schaekers (imec)</i>	535
Effect of Film Thickness on Resistance Switching Characteristics for Cu/NiO/Pt Structure <i>Y. Zhang, K. Zhang, W. Fang, X. Wei, and J. Zhao (Tianjin University of Technology)</i>	541
Optical Constants of ZnO Films <i>B. Huang and H. Yang (Jinan University)</i>	547
Influence of the Pressure on ZnO:Al Film Deposited by DC Magnetron Reactive Sputtering <i>S. Yu, H. Yang, B. Huang, J. Shi, and L. Zeng (Jinan University)</i>	551
Study of the Electrical and Optical Properties of the Silicon Carbide Thin Film <i>R. Luo, H. Yang, B. Huang, and B. Y. Xu (Jinan University)</i>	557
Influence of Vacuum-Annealing Temperature on the Properties of Direct Current (DC) Magnetron Sputtered ZAO Thin Films <i>J. Shi, H. Yang, B. Huang, B. Xu, and S. Yu (Jinan University)</i>	563
Study of Phosphorus Out-Diffusion from High Density Plasma CVD Phosphosilicate Glass Process <i>L. Min, Z. Ying, and Q. Xu (Semiconductor Manufacturing International Corporation)</i>	567

Effects of Substrate Temperature on Resistive Switching of TiO<sub>X</sub> Thin Film 571  
*L. Wang, K. Zhang, W. Fang, and K. Song*  
*(Tianjin University of Technology)*

Electrical and Optical Properties of Zinc Oxide Thin Films Deposited by 577  
Magnetron Sputtering  
*X. Ding and Y. Lai (Fuzhou University)*

A Highly Conductive Bimodal Isotropic Conductive Adhesive and Its 583  
Reliability  
*D. Li, H. Cui, S. Chen, Q. Fan, Z. Yuan (Shanghai University), L. Ye*  
*(SHT Smart High Tech AB), and J. Liu (Shanghai University)*

### **Chapter 5** **CMP and Post-CMP Cleaning**

Challenges and Mechanisms of CMP Slurries for 32nm and Beyond 591  
*H. Morinaga and K. Tamai (Fujimi Incorporated)*

A Study on Optimized Conditioner for Soft Pad in Cu Barrier Removal 597  
*S. Yoon and J. H. Lee (Ehwa Diamond Ind. Co. Ltd.)*

Overcome Challenges in TSV CMP via Slurry Formulation 603  
*K. Luo, C. Wang, J. Jing, and S. Xu*  
*(Anji Microelectronics (Shanghai) Co., Ltd.)*

Investigation on the Correlationship between Process Performances and 609  
Composition of CMP Slurry Designed for GST Alloy Polishing  
*K. Pang (Anji Microelectronics (Shanghai) Co., Ltd.), F. Chen, L. Jiang,*  
*M. Li, and M. Zhong*  
*(Semiconductor Manufacturing International Corporation)*

Fundamental Characterization Studies of Condensed Chemical Mechanical 615  
Polishing Waste Slurry  
*Y. Yamada, M. Kawakubo, S. Watanabe, and T. Sugaya (Hitachi, Ltd.)*

Correlation of Pad Topography, Friction Force and Removal Rate during 621  
Tungsten Chemical Mechanical Planarization  
*Y. Sampurno, A. Rice, Y. Zhuang, and A. Philipossian*  
*(The University of Arizona)*

Tribological and Kinetical Analysis of Barrier Metal Polishing for Next Generation Copper Interconnects <i>R. Duyos Mateo, X. Gu, T. Nemoto, S. Sugawa (Tohoku University), Y. Zhuang (Araca Incorporated), Y. Sampurno, A. Philipossian (The University of Arizona), and T. Ohmi (Tohoku University)</i>	627
Finite Element Analysis (FEA) of Pad Deformation Due to Diamond Disc Conditioning in Chemical Mechanical Polishing (CMP) <i>E. Baisie (North Carolina Agricultural &amp; Technical State University), B. Lin (Tianjin University), X. Zhang (Seagate Technology), and Z. Li (North Carolina Agricultural &amp; Technical State University)</i>	633
Data Driven CMP Manufacturing Modeling for Process and Design Optimization <i>L. J. Song and V. Mehrotra (Ascertain LLC)</i>	639
Ge- and III/V-CMP for Integration of High Mobility Channel Materials <i>P. Ong, L. Witters, N. Waldron, and L. Leunissen (imec)</i>	647
Advanced Direct-Polish Process on Organic Non-Porous Ultra Low-k Fluorocarbon Dielectric on Cu Interconnects <i>X. Gu, T. Nemoto, Y. Tomita, R. Duyos Mateo, A. Teramoto, S. Kuroki, S. Sugawa, and T. Ohmi (Tohoku University)</i>	653
Effect of Slurry Application/Injection Methods and Polishing Conditions on Bow Wave Characteristics <i>X. Liao, Y. Sampurno, Y. Zhuang (The University of Arizona), F. Sudargho (Araca, Inc.), A. Rice, and A. Philipossian (The University of Arizona)</i>	659
Evolution of Post CMP Cleaning Technology <i>G. Banerjee (Air Products)</i>	665
Cleaning Aspects of Novel Materials after CMP <i>R. Vos (imec), M. Wada (Dainippon Screen Mfg. Co.), S. Arnauts, H. Takahashi, D. Cuypers, H. Struyf, and P. Mertens (imec)</i>	671
Study on the Ring Type Crater Defect Reduction in Cu CMP Process <i>J. Xu, P. Lin, C. Xing, P. Li, and Z. Ma (Semiconductor Manufacturing International Corporation)</i>	677
New Application of Optical Endpoint System: In Situ Cu Residue Detection <i>W. Zhang, X. Wang, C. Tan, S. Wang (Applied Materials China), W. Shen (Applied Materials USA), and G. Ge (Semiconductor Manufacturing International Corporation)</i>	683

The Mechanism of Organic Base and Surfactant in Silicon Wafer CMP Process <i>L. Weiwei (Hebei University of Technology)</i>	691
Modeling Copper Chemical Mechanical Polishing Processes Using Linear System Method <i>L. Wu and C. Yan (Lanzhou University of Technology)</i>	699
Effect of pH on CMP of VOx Thin Films for RRAM <i>Y. Liguo, K. Zhang, W. Fang, X. Wei, and Z. Tao Feng (Tianjin University of Technology)</i>	705
Study of Inhibition effects on Copper CMP Slurry Performance <i>J. Jing (Anji Microelectronics (Shanghai) Co., Ltd.), Z. Ma, P. Li, C. Lu, P. Lin (Semiconductor Manufacturing International Corporation), J. Zhang, and X. Cai (Anji Microelectronics (Shanghai) Co., Ltd.)</i>	711

## **Chapter 6** **Materials and Process Integration for Device and Interconnection**

SiON Gate Dielectric Optimization for NBTI Improvement <i>Y. Chen, Y. He, W. Wang, R. Guo, Z. Tang, J. Liu, J. Wu, and J. Ju (Semiconductor Manufacturing International Corporation)</i>	719
Analysis of the Temperature Dependence of Trap-Assisted-Tunneling in Ge pFET Junctions <i>M. Bargallo Gonzalez, G. Eneman, G. Wang, B. De Jaeger, E. Simoen, and C. Claeys (imec)</i>	725
eSiGe Global and Micro Loading Effect Study in High Performance 45nm CMOS Technology <i>Y. He, H. Tu, J. Lin, H. Song, J. Wang, G. Ma, W. Xu, B. Ye, T. Yu, and J. Wu (Semiconductor Manufacturing International Corporation)</i>	731
Investigation of Laser Spike Anneal Dwell Time and It's Compatibility with Embedded-SiGe <i>Y. He, Y. Chen, J. Lu, J. Wu, C. Xu, T. Yu (Semiconductor Manufacturing International Corporation), D. M. Owen, Y. Zhang, and S. Shetty (Ultratech)</i>	737
A Robust Shallow Trench Isolation High Density Plasma Chemical Vapor Deposition Void Free Process for 0.13 $\mu$ m CMOS Technology <i>G. Ning, P. Lin, C. Xing, A. Bian, H. Zhao, and Y. Cao (Semiconductor Manufacturing International Corporation)</i>	743

CMP-Less Planarization Technology with SOG/LTO Etchback for Low Cost 70nm Gate-Last Process	749
<i>H. Yin, L. Men, T. Yang, G. Xu, Q. Xu, C. Zhao, and D. Chen (Chinese Academy of Sciences)</i>	
Etch and Wet Clean Challenges and Joint Optimization	755
<i>B. Yen, J. Lin, C. Lee, M. Hegarty, and P. Loewenhardt (Lam Research Corporation)</i>	
Growth and Processing Defects in CMOS Homo- and Hetero-Epitaxy	761
<i>E. Simoen, M. Bargallo Gonzalez, G. Eneman, E. Rosseel, A. Y. Hikavyy, D. Kobayashi, R. Loo, M. Caymax, and C. Claeys (imec)</i>	
Precise Control of Spike Anneal Process for Advanced CMOS	769
<i>Z. Zhao, J. Tang, and G. Zhao (Applied Materials China)</i>	
Improving Copper Interconnect Reliability via Ta/Ti Based Barrier	775
<i>X. Hu, P. Lin, J. Ma, J. Jiang, and P. He (Semiconductor Manufacturing International Corporation)</i>	
Glue Layer Study of Inter Via between Cu and Al Metal Lines	781
<i>J. Chen, C. Qiao, L. Yang, and K. Chang (Semiconductor Manufacturing International Corporation)</i>	
The Influence of The SIN Cap Process on The Voltage Breakdown and Electromigration Performance of Dual Damascene Cu Interconnects	787
<i>Y. Cao, C. Xing, N. Xu, H. Zhou, A. Bian, and P. Lin (Semiconductor Manufacturing International Corporation)</i>	
Effect of RF Power on Carbon Nanotubes Synthesized at Low Temperature by RF PECVD	793
<i>X. Lin, K. Zhang, K. Hu, X. Qiang, and S. Wang (Tianjin University of Technology)</i>	
Improving Yield with High-Performance Cables	799
<i>P. Warren (W. L. Gore &amp; Associates)</i>	
Study on the Reliability of Fast Curing Isotropic Conductive Adhesive	805
<i>W. Du, H. Cui, S. Chen, Z. Yuan (Shanghai University), L. Ye (SHT Smart High Tech AB), and J. Liu (Shanghai University)</i>	
The Effect of Functionalized Silver on Rheological and Electrical Properties of Conductive Adhesives	811
<i>Q. Fan, H. Cui, C. Fu, D. Li, X. Tang, Z. Yuan (Shanghai University), L. Ye (SHT Smart High Tech AB), and J. Liu (Shanghai University)</i>	

## Chapter 7

### Packaging and Assembly

Microstructural Evolution of Sn3.0Ag0.5Cu3.0Bi0.05Cr/Cu Solder Joints During Thermal Aging and Its Effects on Mechanical Properties <i>F. Lin, W. Bi, G. Ju, and X. Wei (Shanghai University)</i>	819
Study of EMC for Cu Bonding Wire Application <i>T. Takeda, H. Seki, S. Itoh, and S. Zenbutsu (Sumitomo Bakelite Co., Ltd.)</i>	825
Corrosion of Gold and Copper Ball Bonds <i>C. D. Breach (ProMat Consultants), H. Ng, T. Lee (ITE College Central), and R. Holliday (World Gold Council)</i>	831
Cost-effective Use of Gold Wire in Semiconductor Packaging <i>C. J. Vath III (ComSol Consulting Pte. Ltd.) and R. Holliday (World Gold Council)</i>	843
Copper Wire Bonding in High Volume Manufacturing <i>B. K. Appelt, A. Tseng, Y. Lai, and C. Chen (ASE Group)</i>	857
MUF Technology Development for SiP Module <i>Y. Kweon, J. Ha, K. Kim, M. Jang, J. Doh, C. Lee, and D. Yoo (Samsung Electro-Mechanics Co.)</i>	865
Multi Beam Grooving and Full Cut Laser Dicing of IC Wafers <i>J. V. Borkulo and R. Hendriks (Advanced Laser Separation International NV)</i>	873
Advanced Bump Structure for Improving the Board Level Characteristics of WLCSP <i>C. Lee, J. Choi, J. Kim, S. Choi, D. Yoo, S. Park, and Y. Kweon (Samsung Electro-Mechanics Co.)</i>	879
Plasma Cleaning Effect on Automotive Devices <i>Y. P. Chew and T. Aw (Infineon Technologies Sdn Bhd)</i>	887
Packaging Issues for High-Voltage Power Electronic Modules <i>S. S. Ang, T. Evans, J. Zhou, K. Schirmer, H. Zhang, B. Rowden, J. Balda, and A. Mantooth (University of Arkansas)</i>	893

## Chapter 8

### Metrology, Reliability and Testing

IDQ Test Practice in Nanotechnologies <i>S. X. Ye, C. Shen, Z. Liu, and Q. Liyun (Availink, Inc.)</i>	901
Cost-Effective and Accurate Solution for Jitter Performance Test in High-Speed Serial Links <i>M. Lu (Verigy)</i>	907
Plasma Etching for Failure Analysis of Integrated Circuit Packages <i>J. Tang, J. Schelen, and C. Beenakker (Delft University of Technology)</i>	913
Process Optimization of Contact Module in NOR Flash Using High Resolution e-Beam Inspection <i>H. C. Liao, C. L. Hung, T. Luoh, L. Yang, T. Yang, K. Chen, and C. Lu (Macronix International Co., Ltd.)</i>	919
Verification of Systematic Defects Using e-Beam Defect Review System <i>T. Luoh, L. Yang, T. Yang, K. Chen, and C. Lu (Macronix International Co., Ltd.)</i>	925
Determining Coherence length of X-ray Beam Utilizing Line Grating Structures <i>H. Lee, C. L. Soles, and W. Wu (National Institute of Standards and Technology)</i>	931
TSV/3DIC Profile Metrology Based on Infrared Microscope Image <i>J. Tang (Southern Taiwan University), Y. Lay, L. Chen, and L. Lin (National Cheng Kung University)</i>	937
Endpoint Detection in Plasma Etching Using Principal Component Analysis and Expanded Hidden Markov Model <i>M. Kim, S. Kim, S. Zhao, S. Hong, and S. Han (Myongji University)</i>	943
Improvement of In-line SCD Metrology on BEOL Copper CMP Erosion Layers for 65nm Technology Node Logic Production Application <i>C. Rong, Z. Wang, Z. Yin (Semiconductor Manufacturing International Corporation), Z. Tan (KLA-Tencor FaST Division), and L. Zhao (KLA-Tencor China)</i>	949
Spectral Sensitivity Analysis of OCD Based on Muller Matrix Formulism <i>S. Yaoming, Z. Zhensheng, L. Guoxiang, L. Zhijun, and X. Yiping (Raintree Scientific Instruments (Shanghai) Corp.)</i>	955

A Method to Determine Process Capability Cpk and Corresponding Percentage of Non-Conforming for Non-Normally Distributed and Limited Production Data <i>S. F. Yang (Semiconductor Manufacturing International Corporation)</i>	961
High Voltage Device Negative Bias Temperature Instability Improvement with Different Process Conditions <i>P. Sim, S. Koo, and D. Pal (X-FAB Sarawak Sdn. Bhd.)</i>	967
Study The Mixed-Mode Delamination of The Epoxy/Cu Interface <i>Y. Liu and J. Wang (Fudan University)</i>	973
LDMOS Thermal SOA Investigation of a Novel 800V Multiple RESURF with Linear P-top Rings <i>A. P. Herlambang, G. Sheu (Asia University), Y. Guo (Nanjing University of Posts and Telecommunications), and H. Wasisto (Asia University)</i>	979
Investigation of Lateral Die Crack Failure at Reliability Test <i>Y. Soh, C. Tan, X. Chen (Infineon Technologies (Wuxi) Co. Ltd.), K. Chua (Infineon Technologies (Malaysia) Sdn. Bhd.), R. Du, Y. Xi (Infineon Technologies (Wuxi) Co. Ltd.), and T. Lim (Infineon Technologies (Malaysia) Sdn. Bhd.)</i>	985
Study on the Reliability of Nano-Structured Polymer-Metal Composite for Thermal Interface Material <i>L. Zhang, X. Luo, X. Lu, and J. Liu (Shanghai University)</i>	991
Failure Mechanism and Testing of PCB Pad Cratering <i>D. Xie (Flextronics International USA), M. Cai, B. Wu (Flextronics Manufacturing Zhuhai), D. Geiger, D. Shangguan (Flextronics International USA), and I. Martin (Flextronics)</i>	997

## **Chapter 9** **Emerging Semiconductor Technologies**

FPGA Design with Double-Gate Carbon Nanotube Transistors <i>M. Ben Jamaa, P. Gaillardon (Commissariat a l'Energie Atomique), S. Frégonèse (Université Bordeaux), M. De Marchi, G. De Micheli (Ecole Polytechnique Federale de Lausanne), T. Zimmer (Université Bordeaux), I. O'Connor (Institut des Nanotechnologies de Lyon), and F. Clermidy (Commissariat a l'Energie Atomique)</i>	1005
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Three-Dimensional (3D) Integration Technology <i>T. Ohba (The University of Tokyo)</i>	1011
Electrical Quality of III-V/Oxide Interfaces: Good Enough for MOSFET Devices <i>G. Brammertz, A. Alian, H. Lin, L. Nyns, S. Sioncke, C. Merckling, W. Wang, M. Caymax, and T. Hoffmann (imec)</i>	1017
Low Temperature Bonding with Thin Wafers for 3D Integration <i>T. Matthias (EV Group), B. Kim (EV Group Inc.), P. Kettner, M. Wimplinger, and P. Lindner (EV Group)</i>	1023
Vertical LED with Diamond-Like Carbon Interface for High-Power Illumination <i>J. C. Sung, K. Kan, and M. Sung (SinoDiamond LED)</i>	1029
Alumina Abrasives for Sapphire Substrate Polishing <i>D. Merricks (Ferro Electronic Materials)</i>	1035
Experimental and Modeling on Atomic Layer Deposition Al <sub>2</sub> O <sub>3</sub> /n-InAs Metal-Oxide-Semiconductor Capacitors with Various Surface Treatments <i>H. Trinh, E. Chang (National Chiao Tung University), G. Brammertz (imec), C. Lu, H. Nguyen, and B. Tran (National Chiao Tung University)</i>	1041
Effects of Surface Pretreatments on p-GaN/GZO Contact by rf Magnetron Sputter <i>W. Wang, X. Li, J. Zhang, and J. Zhang (Shanghai University)</i>	1047
A Phase Change Memory Device Fabrication Technology Using Si <sub>2</sub> Sb <sub>2</sub> Te <sub>6</sub> for Low Power Consumption Application <i>Y. Li (Chinese Academy of Sciences), X. Wan (Semiconductor Manufacturing International Corporation), Z. Song (Chinese Academy of Sciences), J. Xie (Semiconductor Manufacturing International Corporation), B. Chen (Silicon Storage Technology, Incorporated), B. Liu (Chinese Academy of Sciences), G. Wu, N. Zhu (Semiconductor Manufacturing International Corporation), M. Zhong (Chinese Academy of Sciences), J. Xu (Semiconductor Manufacturing International Corporation), and Y. Chen (Chinese Academy of Sciences)</i>	1053
Smart Systems <i>T. Gessner, M. Vogel, T. Otto, S. Schulz, and R. Baumann (Fraunhofer Institute for Electronic Nano Systems)</i>	1059

Electrical Characterization of the MOS (Metal-Oxide-Semiconductor) System: High Mobility Substrates	1065
<i>D. Lin, G. Brammertz, S. Sioncke, L. Nyns, A. Alian, W. Wang, M. Heyns, M. Caymax, and T. Hoffmann (imec)</i>	
Characterization and Optical Properties of CdS Thin Films Grown by Chemical Bath Deposition	1071
<i>W. Zhang and S. Cheng (Fuzhou University)</i>	
Electroluminescence of End-Capped Poly[9,9-di-(2'-ethylhexyl)fluorenyl-2,7-diyl] Blended with F8BT	1077
<i>Q. Zhang (University of Electronic Science and Technology of China) and S. Zhang (Xihua University)</i>	
Enhancement of Luminance via Blending F8BT with Tetraphenyldiaminobiphenyl-Containing Hole Transport Polymer	1087
<i>Q. Zhang (University of Electronic Science and Technology of China)</i>	

## **Chapter 10** **Silicon Materials for Electronic and Photovoltaic Applications**

Improvements on the Uniformity of a-Si Solar Thin Films by Using Auxiliary Magnetic Field	1097
<i>L. C. Hu, Y. P. Chen, J. Chang, J. J. Lee, I. Chen, and T. T. Li (National Central University)</i>	
Hydrogenated Silicon Thin Film and Solar Cell Prepared by Electron Cyclotron Resonance Chemical Vapor Deposition Method	1103
<i>C. Lee, J. Chang, Y. Chu, C. Lien, I. Chen, and T. Li (National Central University)</i>	
Properties of Multicrystalline Silicon Wafers Based on UMG Material	1109
<i>T. Jiang, X. Yu, X. Li, X. Gu, P. Wang, and D. Yang (Zhejiang University)</i>	
Defect Evaluation by Photoluminescence for Uniaxially Strained Si-On-Insulator	1117
<i>D. Wang, K. Yamamoto, H. Gao, H. Yang, and H. Nakashima (Kyushu University)</i>	
Effects of Transverse Magnetic Field on Thermal Fluctuations in the Melt of a Cz-Si Crystal Growth	1123
<i>X. Liu, L. Liu, and Y. Wang (Xi'an Jiaotong University)</i>	

Light Trapping for High Efficiency Heterojunction Crystalline Si Solar Cells <i>Q. Wang, Y. Xu, E. Iwaniczko, and M. Page (National Renewable Energy Laboratory)</i>	1129
Fabrication and Quantum Confinement Investigation of Ge Multiple Quantum Wells with Si <sub>3</sub> N <sub>4</sub> Barriers <i>J. Chen, S. Lee, and S. Huang (University of New South Wales)</i>	1135
Structural and Optical Properties of Porous SiGe/Si Multilayer Films <i>B. Zhou, X. Li (Minjiang University), S. W. Pan, S. Y. Chen, and C. Li (Xiamen University)</i>	1145
On the Impact of Heavy Doping on Grown-In Defects in Czochralski-Grown Silicon <i>X. Zhang, W. Xu, J. Chen, X. Ma, D. Yang (Zhejiang University), L. Gong, D. Tian (QL Electronics), and J. Vanhellemont (Ghent University)</i>	1151
The Influence Of Silicon Orientation On Surface Blistering Behaviors for Molecular Hydrogen Ion Implantation <i>Y. Hsiao, J. Liang (National Tsing Hua University), and C. Lin (National Hsinchu University of Education)</i>	1159
Very High Deposition Rate of a-Si:H Thin Films by ECRCVD <i>H. F. Chiu, Y. S. Chang (National Tsing Hua University), J. Y. Wu, Y. S. Li, J. Chang, C. C. Lee, I. Chen (National Central University), C. C. Su (Chung-Shan Institute of Science &amp; Technology), and T. T. Li (National Central University)</i>	1165

#### Author Index